

0.8

0.17

2.5V Drive Nch MOSFET

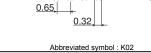
Structure

Silicon N-channel MOSFET

Features

- 1) Low On-resistance.
- 2) High power package.
- 3) 2.5V drive.

TSMTB 3.0 (B) (7) (6) (5) (1) (1) (1) (1) (1) (2) (2) (2) (2) (2)



(2) (3)

14

(1)

Application

Switching

• Packaging specifications

	• •	
	Package	Taping
Туре	Code	TR
	Basic ordering unit (pieces)	3000
QS8K2		0

Parameter		Symbol	Limits	Unit
Drain-source voltage		V _{DSS}	30	V
Gate-source voltage		V _{GSS}	±12	V
Drain current	Continuous	Ι _D	±3.5	А
	Pulsed	^{*1} ا _{DP}	±12	А
Source current	Continuous	I _s	1	А
(Body Diode)	Pulsed	1 ا _{sp}	12	А
Power dissipation		P _D *2	1.5	W / TOTAL
		' D	1.25	W / ELEMENT
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

*1 Pw≤10µs, Duty cycle≤1%

*2 Mounted on a ceramic board.

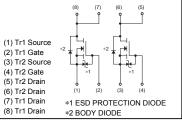
• Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)	83.3	°C / W /TOTAL
	Kiii (Cii-a)	100	°C / W /ELEMENT

* Mounted on a ceramic board.

• Dimensions (Unit : mm)





• Electrical characteristics (Ta = 25°C)

<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	-	-	±10	μA	$V_{GS}=\pm 12V, V_{DS}=0V$
Drain-source breakdown voltage	V (BR)DSS	30	-	-	V	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	-	-	1	μA	V _{DS} =30V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	0.5	-	1.5	V	V _{DS} =10V, I _D =1mA
Statia drain actures an atota	*	-	38	54		I _D =3.5A, V _{GS} =4.5V
Static drain-source on-state resistance	R _{DS (on)}	-	40	56	mΩ	I _D =3.5A, V _{GS} =4V
		-	55	77		I _D =3.5A, V _{GS} =2.5V
Forward transfer admittance	I Y _{fs} I*	3.0	-	-	s	I _D =3.5A, V _{DS} =10V
Input capacitance	C _{iss}	-	285	-	рF	V _{DS} =10V
Output capacitance	C _{oss}	-	90	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	-	55	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	-	8	-	ns	I _D =1.7A, V _{DD} ≒15V
Rise time	t _r *	-	12	-	ns	V _{GS} =4.5V
Turn-off delay time	t _{d(off)} *	-	29	-	ns	R _L =8.8Ω
Fall time	t _f *	-	13	-	ns	$R_G=10\Omega$
Total gate charge	Q _g *	-	4.6	-	nC	I _D =3.5A, V _{DD} ≒15V
Gate-source charge	Q _{gs} *	-	0.7	-	nC	V_{GS} =4.5V R _L =4.3 Ω
Gate-drain charge	Q _{gd} *	-	1.5	-	nC	R_{G} =10 Ω

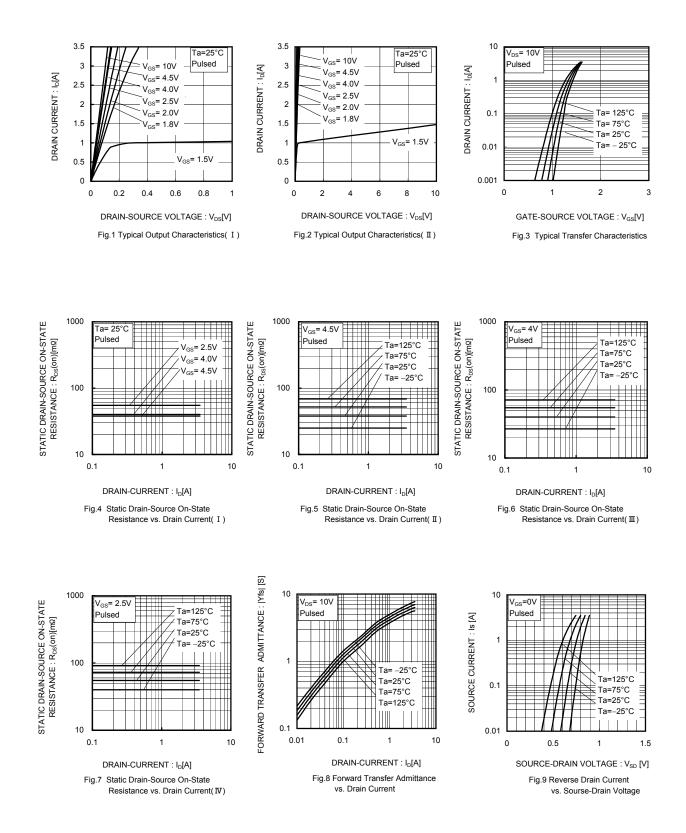
*Pulsed

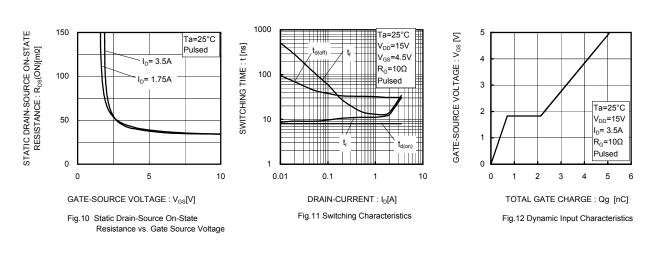
•Body diode characteristics (Source-Drain) (Ta = 25°C)

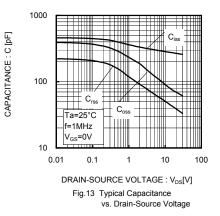
Parameter	Svmbol	Min.	T. m			
	• ,	IVIIII.	Тур.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^{*}	-	-	1.2	V	I _s =3.5A, V _{GS} =0V

*Pulsed

• Electrical characteristic curves







Measurement circuits

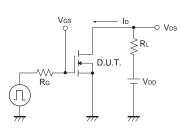


Fig.1-1 Switching time measurement circuit

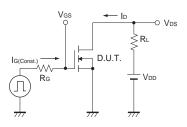


Fig.2-1 Gate charge measurement circuit

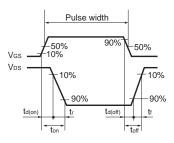


Fig.1-2 Switching waveforms

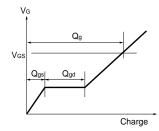


Fig.2-2 Gate Charge Waveform

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